

# Diffraction at GaAs/Fe<sub>3</sub>Si core/shell nanowires: the formation of nanofacets

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## Abstract

GaAs/Fe<sub>3</sub>Si core/shell nanowire structures were grown by molecular-beam epitaxy on oxidized Si(111) substrates and characterized by synchrotron x-ray diffraction. The surfaces of the Fe<sub>3</sub>Si shells exhibit nanofacets. These facets consist of well pronounced Fe<sub>3</sub>Si{111} planes. Density functional theory reveals that the Si-terminated Fe<sub>3</sub>Si{111} surface has the lowest energy in agreement with the experimental findings. We can analyze the x-ray diffuse scattering and diffraction of the ensemble of nanowires avoiding the signal of the substrate and poly-crystalline films located between the wires. Fe<sub>3</sub>Si nanofacets cause streaks in the x-ray reciprocal space map rotated by an azimuthal angle of 30 ° compared with those of bare GaAs nanowires. In the corresponding TEM micrograph the facets are revealed only if the incident electron beam is oriented along  $[1\bar{1}0]$  in accordance with the x-ray results. Additional maxima in the x-ray scans indicate the onset of chemical reactions between Fe<sub>3</sub>Si shells and GaAs cores occurring at increased growth temperatures.

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## I. INTRODUCTION

Nanowires (NWs) that combine a semiconductor and a ferromagnet in a core/shell geometry were investigated recently.[1–6] Those core/shell NWs allow for a magnetization along the wire axis and thus perpendicular to the substrate surface.[7] Magnetic pillars with a magnetization perpendicular to the substrate surface have the potential for circular-polarized light emitting diodes that can optically transmit spin information in zero external magnetic field.[8]

The nucleation of planar crystalline films on substrates can be considered in a similar way as wetting or nonwetting of liquids.[9] If the formation of the film surface and the film-substrate interface leads to an surface energy gain  $\Delta\gamma < 0$  compared to the bare substrate surface, the film wets the substrate and grows layer-by-layer in Frank van der Merwe growth mode. In case of an surface energy expense ( $\Delta\gamma > 0$ ), three-dimensional (3D) islands form in the Volmer-Weber (VW) growth mode, similar to liquid droplets with a finite contact angle.  $\text{Fe}_3\text{Si}$  is lattice matched to GaAs. Nevertheless we observed the strain-free VW island growth mode of  $\text{Fe}_3\text{Si}$  on GaAs.[10] Thus initially isolated islands can adopt their equilibrium shape before coalescence.

Similarly small particles of Au on a MgO substrate e.g. adopt the equilibrium shape with  $\{111\}$  and  $\{100\}$  facets.[11] The equilibrium crystal shape of GaAs in an As-rich environment consists of  $\{111\}$ ,  $\{110\}$  and  $\{100\}$  facets.[12] For the Ga-assisted catalyst-free growth of GaAs NWs by MBE in the  $[111]$  direction only the  $\{110\}$  sidewalls are present for geometrical reasons, as the growth rate of the NWs along  $[111]$  is dominating.[13] However for Au-induced NW growth  $\{111\}$  nanofacets were found in the zincblende sections of the NWs.[14] MBE grown GaAs/AlAs core/shell NWs were decorated by Stranski Krastanov (SK) growth of InAs islands.[15] These islands exhibit  $\{111\}$  and  $\{115\}$  facets and develop preferentially at the  $\langle 112 \rangle$ -oriented corners of the NWs. Ge islands on Si NWs exhibited  $\{111\}$ ,  $\{110\}$  and  $\{113\}$  facets as a result of a SK growth process.[16] Ferromagnetic MnAs islands grow in a strain driven VW growth mode on semiconducting InAs NWs, where the lattice mismatch amounts up to 18 percent.[17] In our system  $\text{Fe}_3\text{Si}/\text{GaAs}$  we can expect a strain-free VW island growth of  $\text{Fe}_3\text{Si}$  on  $\text{GaAs}\{110\}$ .[10] We recently demonstrated that  $\text{GaAs}/\text{Fe}_3\text{Si}$  core/shell NWs prepared by MBE show ferromagnetic properties with a magnetization oriented along the NW axis (i.e. perpendicular to the substrate surface). However,

the structural and magnetic properties of the core/shell NWs depend on the substrate temperature  $T_S$  during the growth of the  $\text{Fe}_3\text{Si}$  shells.[18] For certain growth temperatures a coincidence of the core- and shell-orientations was observed [19], and the  $\text{Fe}_3\text{Si}$  growth is pseudomorphic on GaAs. In addition nanofacetting of the  $\text{Fe}_3\text{Si}$  shells was found. The GaAs cores are usually not free of defects, especially near the Si/GaAs interface and during the late phase of GaAs NW growth planar defects connected to the transition from zincblende to wurtzite segments are found.[20] In this work, we investigate  $\text{Fe}_3\text{Si}$  shells grown around GaAs(111) oriented cores at different substrate temperatures  $T_S$  and analyze the nanofacets induced by strain-free VW growth of  $\text{Fe}_3\text{Si}$  shells using X-ray diffraction (XRD) in grazing incidence geometry, scanning electron microscopy (SEM), and transmission electron microscopy (TEM).

## II. THEORETICAL SECTION

The equilibrium state of the  $\text{Fe}_3\text{Si}$  surface as a function of composition is determined by the minimization of the grand potential  $\Omega$ ,[21, 22] where  $E$  is the energy of the crystal,  $S$  and  $T$  are the entropy and the temperature of the system,  $n_i$  and  $\mu_i$  are the numbers of atoms of sort  $i$  and the corresponding chemical potentials.

$$\Omega = E - TS - \sum n_i \mu_i, \quad (1)$$

This minimization is usually performed for the temperature  $T = 0$ . In other words the stability of the surface (i.e. its crystallographic orientation and its surface termination or chemical configuration) is given by its surface energy per unit area  $\gamma$ , which is a free energy expressed with respect to the chemical potentials  $\mu_i$ , which represent reservoirs of the chemical species involved. This means:

$$\gamma \cdot A = E_t - n_{Fe} \mu_{Fe} - n_{Si} \mu_{Si}, \quad (2)$$

where  $A$  is the area of the surface unit cell,  $E_t$  is its total energy, and  $n_{Fe}$  and  $n_{Si}$  are the numbers of Fe and Si atoms in the cell. We assume the surface to be in thermodynamic equilibrium with the bulk material. This implies that  $3\mu_{Fe} + \mu_{Si} = g_{\text{Fe}_3\text{Si}}$ , the energy per formula unit of bulk  $\text{Fe}_3\text{Si}$ . [23, 24] This constraint implies that  $\gamma$  can be expressed as a function of just one independent variable e.g.  $\mu_{Si}$ . On the other hand the individual

atomic chemical potentials can never exceed the energy of the condensed pure element, i.e. the energy per atom in bulk Fe and bulk Si. The three constraints jointly place an upper and lower limit on  $\mu_{Si}$ . Density functional theory (DFT)[25–29] in the generalized gradient approximation[30] was applied in order to determine the surface energy of low index surfaces using the Vienna Ab Initio Simulation Package (VASP).[31, 32] The calculations were performed in a slab geometry using slabs from 12 to 16 Å thick and a vacuum region of 10 Å. All atomic positions were relaxed except the innermost 3-4 layers, until the largest force component on every atom was below 0.05 eV Å<sup>-1</sup>. All of the calculations assumed a fully ordered ferromagnetic Fe<sub>3</sub>Si lattice.

### III. EXPERIMENTAL SECTION

GaAs/Fe<sub>3</sub>Si core/shell NW structures were grown by MBE on Si(111) substrates. First, GaAs NWs are fabricated by the Ga-assisted growth mode on Si(111) substrates covered with a thin native oxide layer. The growth mechanism is the vapor-liquid-solid (VLS) mechanism,[33–37] where pin holes in the SiO<sub>2</sub> serve as nucleation sites.[38] A Ga droplet is the preferred site for deposition from the vapor. The GaAs NW then starts to grow by preferential nucleation at the spatially restricted GaAs/Si interface. The GaAs NWs are grown at a substrate temperature of 580 °C, with a V/III flux ratio of unity and an equivalent two-dimensional growth rate of 100 nm/h. Once the GaAs NW templates are grown, the sample is transferred under ultra high vacuum conditions to an As free growth chamber for deposition of the ferromagnetic films. There the GaAs NW templates are covered with Fe<sub>3</sub>Si shells at substrate temperatures varying between 100 °C and 350 °C. More details regarding the growth conditions can be found in Ref. [7].

The resulting core/shell NW structures were characterized by SEM, X-ray diffraction, and TEM. The X-ray experiments were performed in grazing incidence geometry at the beamline BM 02 of the European Synchrotron Radiation Facility (ESRF) in Grenoble. The energy of the beam was 10 keV and the detector was an area detector S70 from Imxpad. The detector size is 560×120 pixels of size 130×130 μm<sup>2</sup> each. In order to minimize the penetration depth into substrate and parasitic film between the NWs a very small angle of incidence of 0.04 ° was chosen.[39] In this way the signal of the ensemble of NWs was always dominating the diffraction pattern. This was checked by observation of the vanishing

signal of the single-crystal Si substrate, which would dominate the diffraction curve at larger angles of incidence.

The TEM specimens are prepared by mechanical lapping and polishing, followed by argon ion milling according to standard techniques. TEM images are acquired with a JEOL 3010 microscope operating at 300 kV. The cross-section TEM methods provide high lateral and depth resolutions on the nanometer scale. It has to be considered that TEM imaging of NWs corresponds to two-dimensional projections along electron beam direction.

#### IV. RESULTS AND DISCUSSION

In SEM micrographs a relatively low area density of well oriented NWs of  $\sim 5 \times 10^8 \text{ cm}^{-2}$  is found. In 1 SEM top views of a GaAs core NW and a GaAs/Fe<sub>3</sub>Si core/shell NW ( $T_S = 200 \text{ }^\circ\text{C}$ ) are given together with a side-view of a core/shell NW. Regular step patterns, facets, are clearly visible on the sidewalls of the NW. At the top of the NW a thinner part is visible. During the last stage of GaAs NW growth no Ga is supplied, and so the remaining Ga in the droplet on top of the NWs is consumed, leading to an elongation of the NW at reduced diameter. In addition 1 illustrates the orientation of the  $\{11\bar{1}\}$  shell facets with respect to the cores. A hexagonal prism symbolizing the GaAs NWs with  $\langle 110 \rangle$ -oriented sidewalls is drawn schematically. In addition a tetrahedron depicting the equilibrium shape of Fe<sub>3</sub>Si crystallites consisting of Fe<sub>3</sub>Si $\{11\bar{1}\}$  planes is shown. The tilted Fe<sub>3</sub>Si $\{11\bar{1}\}$  planes form extended shell facets. These facets are intersecting the top Fe<sub>3</sub>Si(111) plane, which is parallel to the substrate surface. This results in the formation of triangular features at the top which are observed by SEM.

2 (a) depicts the XRD curves of the  $(\bar{2}20)$  reflection of GaAs/Fe<sub>3</sub>Si core/shell NWs,  $T_S = 200 \text{ }^\circ\text{C}$ . A radial  $\omega/2\theta$ -scan (thick line) along the  $[\bar{1}10]$  direction and an angular  $\omega$ -scan perpendicular to the  $[\bar{1}10]$  direction (thin line), together with their full widths at half maximum (FWHM) are given. The radial scan shows thickness fringes (marked by arrows) corresponding to a thickness of 14.3 nm equal to the Fe<sub>3</sub>Si shell thickness (cf. 4 (b)). The radial scan has a FWHM of  $0.08^\circ$  whereas the angular scan has a larger width of  $0.55^\circ$ . The FWHM in angular direction here corresponds to the range of twist of the NWs, as in-plane reflections are used.[40] The range of tilt of GaAs NWs was measured to be near  $(0.28 \pm 0.1)^\circ$  using symmetrical out-of-plane measurements.

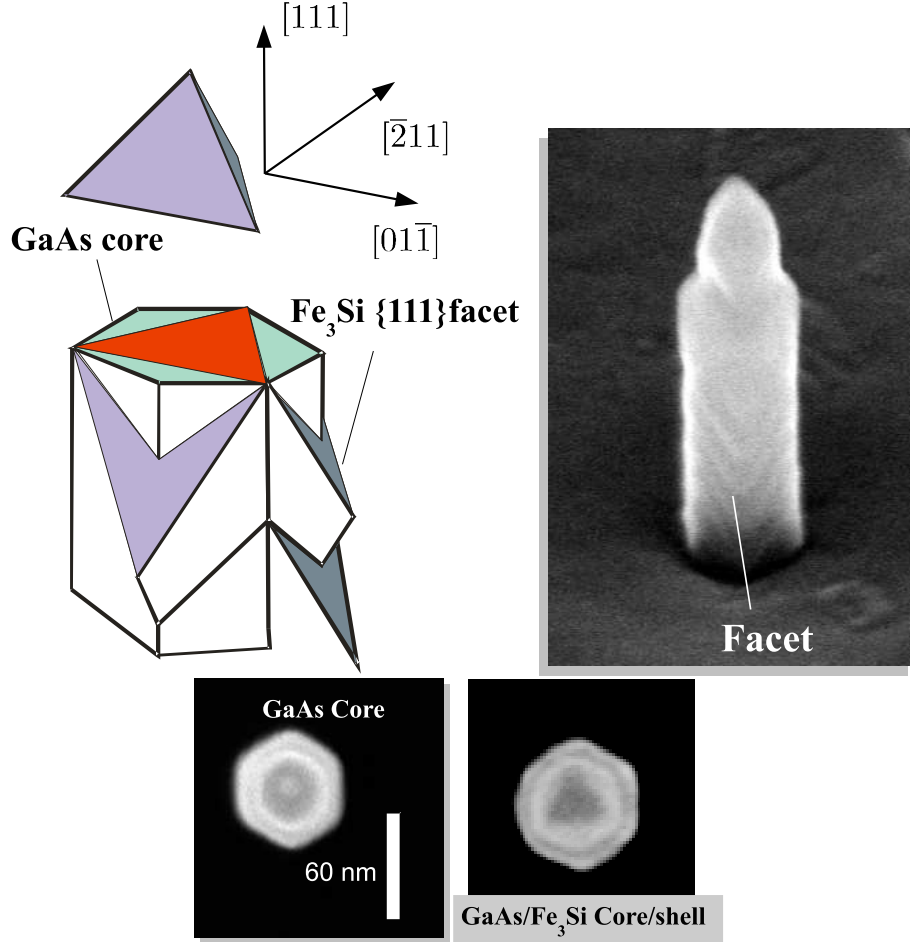


Figure 1. (color online) SEM side view of a core/shell NW (right side) and SEM top views of a core and core/shell NWs (below) grown at  $T_S = 200$  °C. A sketch of the GaAs core and the  $\text{Fe}_3\text{Si}$  shells (left side) with tilted  $\{11\bar{1}\}$  facets is illustrating schematically the orientation relationship between the cores and the facets. In addition a tetrahedron consisting of  $\{111\}$  planes is given.

2 (b) and (c) show XRD curves of GaAs/ $\text{Fe}_3\text{Si}$  core/shell NWs,  $T_S = 200$  °C. Radial  $\omega/2\theta$ -scans along (b) the  $\langle 110 \rangle$  and (c) the  $\langle 211 \rangle$  directions are given. Scan (b) does not reveal any unexpected maxima due to polycrystalline material whereas scan (c) exhibits additional maxima caused by the wurtzite regions in the GaAs cores. Merely the (400) maximum points to another orientation of some of the crystallites probably caused by additional twins in the cores that are not parallel to the GaAs/Si interface. The detection of the wurtzite regions in the GaAs cores again points to the fact, that our measurements are sensitive for the core/shell NWs only. In a similar scan for a sample grown at 300 °C we observed diffraction maxima evidencing chemical reaction between cores and shells.

3 demonstrates in-plane reciprocal space maps of the  $(\bar{2}20)$ -reflection of GaAs NWs (left) and GaAs/Fe<sub>3</sub>Si core/shell NWs (center and right) grown by MBE on a Si(111) substrate. The growth temperatures of the Fe<sub>3</sub>Si shells were 200 °C (center) and 300 °C (right). The crystallographic directions are sketched below. The radial direction ( $\omega/2\Theta$ ) of the scans is vertical and the angular direction ( $\omega$ ) horizontal. The facets of the pillar shaped cores with hexagonal cross section are clearly distinguished by streaks in the diffuse scattering pointing along the  $\langle 110 \rangle$  directions. Remarkably, in the central map core streaks along the  $\langle 110 \rangle$  directions are still visible although they are superimposed by additional streaks along the  $\langle 1\bar{2}1 \rangle$  directions originating from the facets of the Fe<sub>3</sub>Si shells. In the map shown on the right side only streaks of the shell facets remain. Additional maxima above the main peak indicate chemical reactions between Fe<sub>3</sub>Si and GaAs occurring at  $T_S = 300$  °C near the interface similar as those observed for planar films on GaAs.[41, 42]

4 shows a multi-beam bright-field TEM micrograph, illustrating the orientations of the Fe<sub>3</sub>Si facets of the core/shell NW on Si(111). In 4(a) the incident electron beam is oriented along  $[1\bar{1}0]$  in (b) along  $[11\bar{2}]$ . In (a) we observe facets of the Fe<sub>3</sub>Si shell in (b) we see smooth interfaces and surfaces. The roughening due to the facetting is not observed along this direction. The visibility of the thickness fringes in 2 points to the fact, that (1) we really measure the diffraction signal of the core/shell NWs only, and (2) that the thickness fringes are measured in an  $(\omega/2\Theta)$ -scan along the  $[1\bar{1}0]$  direction where the interfaces are smooth. A growth temperature of 200 °C results in this highly perfect Fe<sub>3</sub>Si shell structure.

The  $(11\bar{1})$  surface nanofacets are expected to be inclined to the  $(110)$  cladding planes of the GaAs cores leading to an increase of the surface area A. There is a non negligible material transport over distances small compared to the NW lengths. On a larger length-scale the Fe<sub>3</sub>Si shell is approximately reproducing the shape of the GaAs core NWs.[18] The straight horizontal contrasts in the GaAs cores in (a) are caused by planar defects leading to alternating zincblende and wurtzite GaAs regions.

5 shows results of DFT calculations of surface energies of the Fe<sub>3</sub>Si shells for a wide range of chemical potentials and several possible surface terminations. Fe<sub>3</sub>Si surfaces were found to be Si-rich.[43, 44] In that case the Si-terminated Fe<sub>3</sub>Si(111) planes are most favorable energetically, even if geometrical factors, i.e. the inclination angle between GaAs(110) and Fe<sub>3</sub>Si(111) planes of  $\psi = 35.3$  °, are taken into account. The  $(110)$  surface has an energy of  $\gamma_{110} = 140 \text{ meV} \cdot \text{\AA}^{-2}$ . Hence the criterion for  $(111)$  facet formation is that the  $(111)$  surfaces

have an energy less than  $\gamma_{110} \cdot \cos(\psi) = 114.25 \text{ meV} \cdot \text{\AA}^{-2}$ . As a result our DFT calculations confirmed that the formation of facets reduces the overall surface energy.

## V. CONCLUSIONS

Layer-by-layer growth could in principle solve the problem of nanofacetting. However, even planar  $\text{Fe}_3\text{Si}$  grows on  $\text{GaAs}(001)$  in the strain-free VW island growth mode.[10] Poor wetting during the nucleation of  $\text{Fe}_3\text{Si}$  on  $\text{GaAs}$  leads initially to isolated islands, despite of perfect lattices match. We supported the hypothesis that the nanofaceted  $\text{Fe}_3\text{Si}$  shells found in the present work are a result of VW island growth. The role of the surface is more important for NWs than for planar films, the faceted growth of the lattice matched shells is an example for such surface related phenomena. Facetting will also play a role in systems with SK growth mode and strain-driven VW island growth.

$\text{GaAs}$  core NWs were grown on the oxidized  $\text{Si}(111)$  surface inside holes of the  $\text{SiO}_2$  film via the VLS growth mechanism. Then ferromagnetic  $\text{Fe}_3\text{Si}$  shells were grown resulting in continuous covering of the cores. A polycrystal film grew unintentionally between the NWs. We have successfully avoided the XRD signal of the polycrystal film by studying the ensemble of core/shell NWs using x-ray grazing incidence diffraction geometry. We did not observe additional orientations of the shell with respect to the core, i.e. the shells are pseudomorphic. Up to a growth temperature of  $200 \text{ }^\circ\text{C}$  additional broadening of the shell diffraction maxima compared to those of the cores is rather limited. The analysis of the x-ray diffuse scattering revealed the hexagonal cross-section of the  $\text{GaAs}$  cores. In addition  $\text{Fe}_3\text{Si}$  nano-facets of the shells cause streaks rotated by an azimuthal angle of  $30 \text{ }^\circ$ . The nano-facets consist e.g. of  $\{111\}$  planes tilted around  $\langle 011 \rangle$  axes towards the  $\langle 211 \rangle$  direction, i.e. for  $[111]$  oriented NWs the  $(\bar{1}11)$  facets are most pronounced, forming a regular pattern along the  $\text{GaAs}$  NWs. The  $\{111\}$  facets of  $\text{Fe}_3\text{Si}$  are formed because under our Si-rich conditions they have the lowest surface energy in agreement with the DFT calculations.

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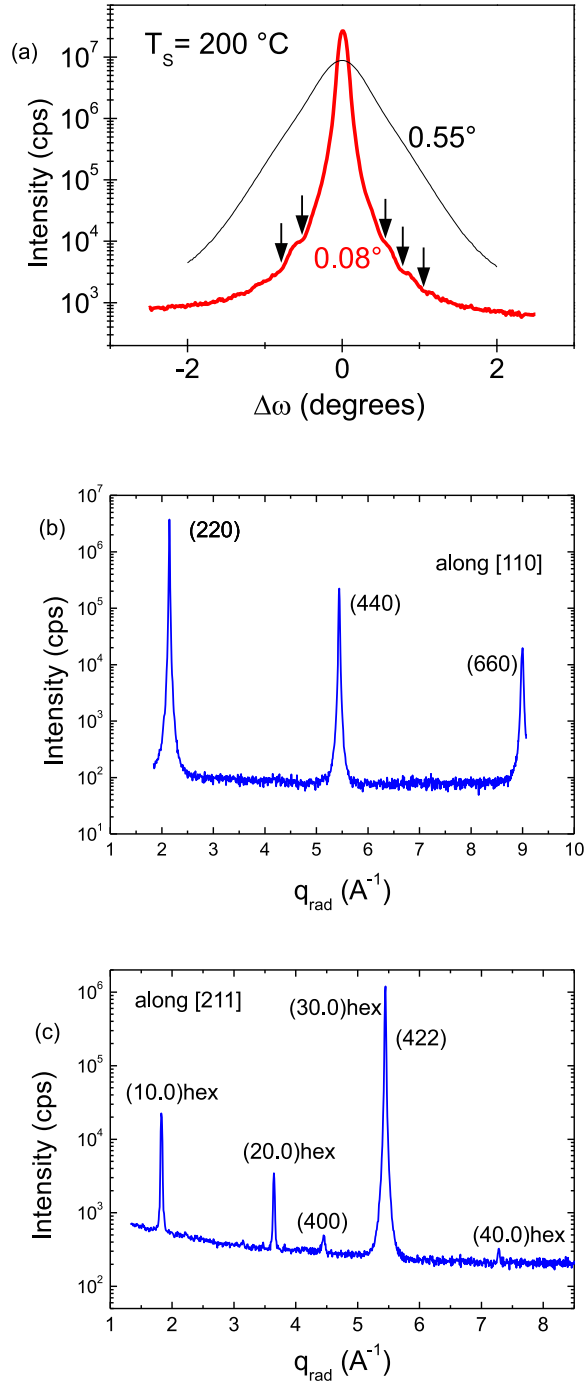


Figure 2. (color online) (a) XRD curves of the  $(\bar{2}20)$  reflection of GaAs/Fe<sub>3</sub>Si core/shell NWs,  $T_S = 200$  °C. A radial  $\omega/2\theta$ -scan (thick red line) along the  $[\bar{1}10]$  direction and an angular  $\omega$ -scan perpendicular to the  $[\bar{1}10]$  direction (thin black line), together with their full widths at half maximum (FWHM) are given. Thickness fringes are marked by arrows. (b) and (c) radial XRD  $\omega/2\theta$ -scans along  $\langle 110 \rangle$  (b) and  $\langle 211 \rangle$  (c) over a wider range than (a).

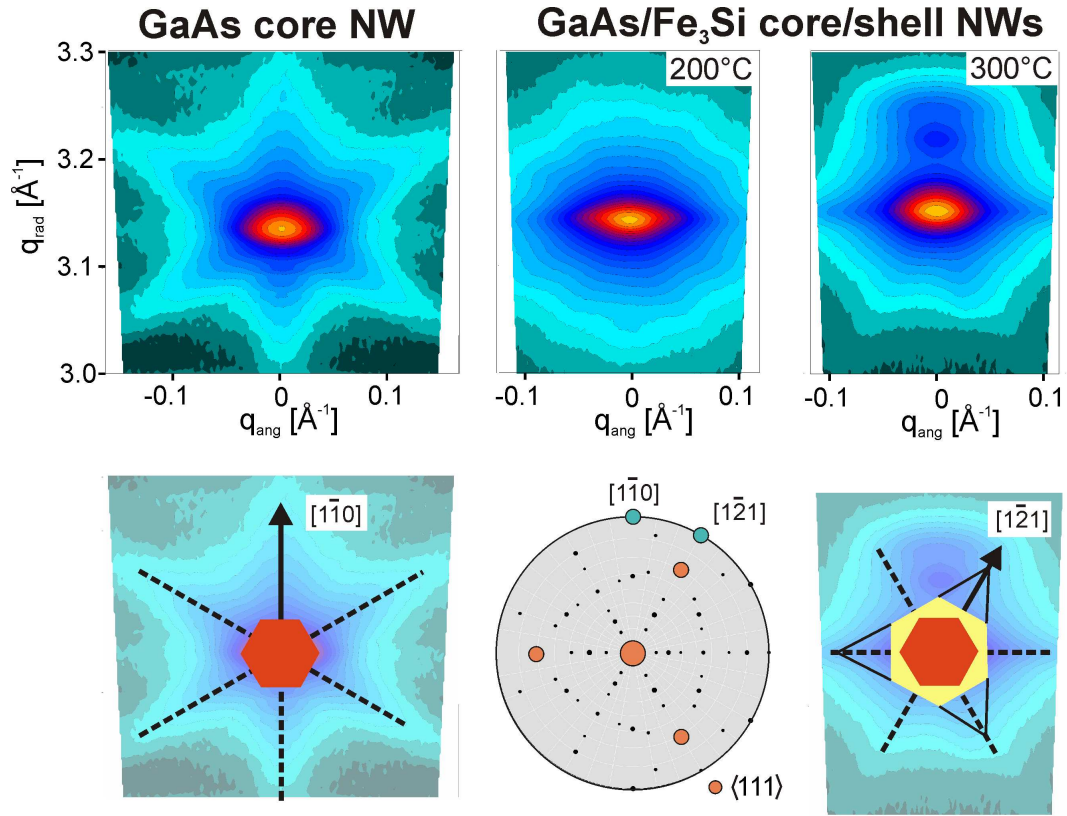


Figure 3. (color online)  $(\bar{2}20)$  in-plane reciprocal space maps of  $[111]$ -oriented GaAs NWs (upper left) and GaAs/Fe<sub>3</sub>Si core/shell NWs (upper center and upper right) grown by molecular beam epitaxy on Si(111). The growth temperatures of the Fe<sub>3</sub>Si shells are given above. The crystallographic directions together with the corresponding sidewalls are sketched below. In the symbolic stereogram (middle) the  $[1\bar{1}0]$  and  $[1\bar{2}1]$  directions are marked by blue circles and the different  $\{111\}$  directions by red circles. The radial direction of the scans is drawn vertically and the angular direction is directed horizontally in the figure.

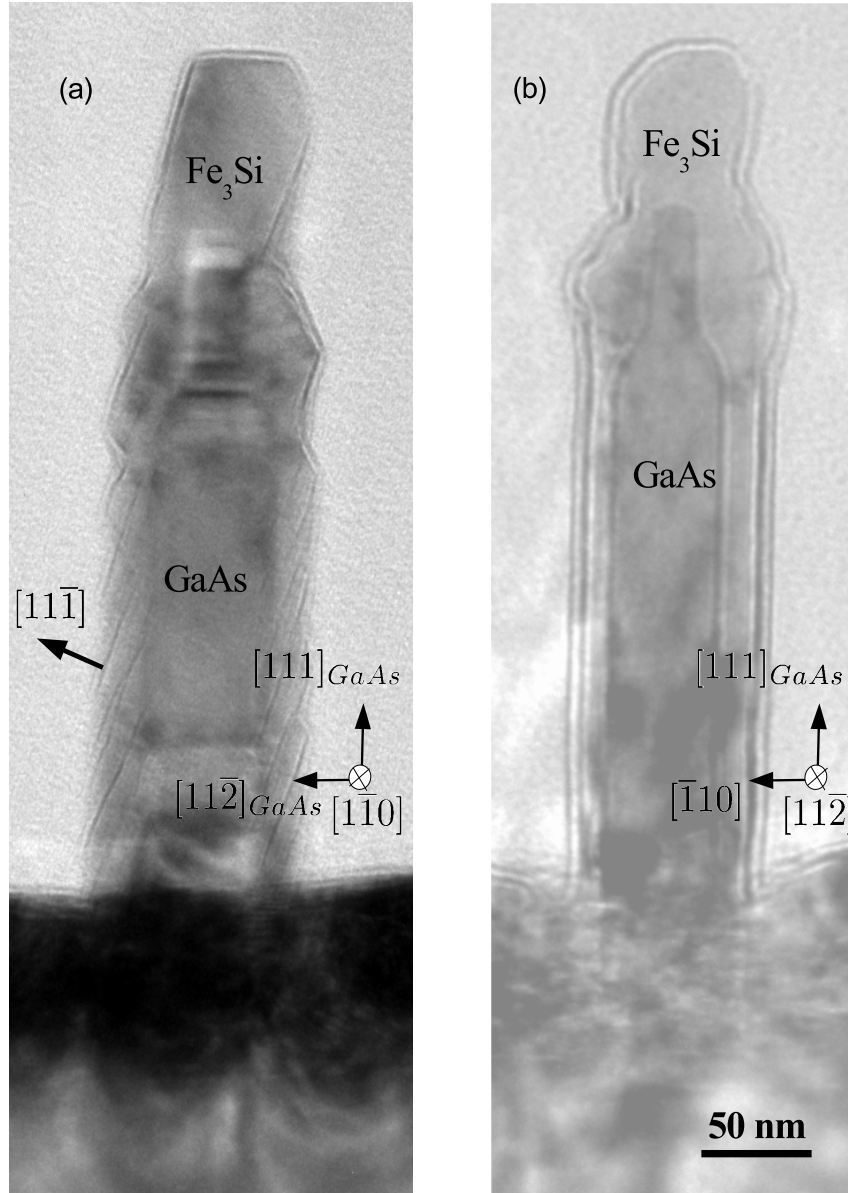


Figure 4. Multi-beam bright-field TEM micrographs illustrating the orientations of the Fe<sub>3</sub>Si shell facets with respect to the GaAs cores. The cores and shells are distinguished clearly. For the  $[1\bar{1}0]$  direction of the electron beam (a) we see facets corresponding to tilted  $(11\bar{1})$  planes as sketched in 1. When the electron beam is running along the  $[11\bar{2}]$  direction no facets are observed (b). The images are slightly defocused in order to increase the contrast of the surfaces and interfaces.

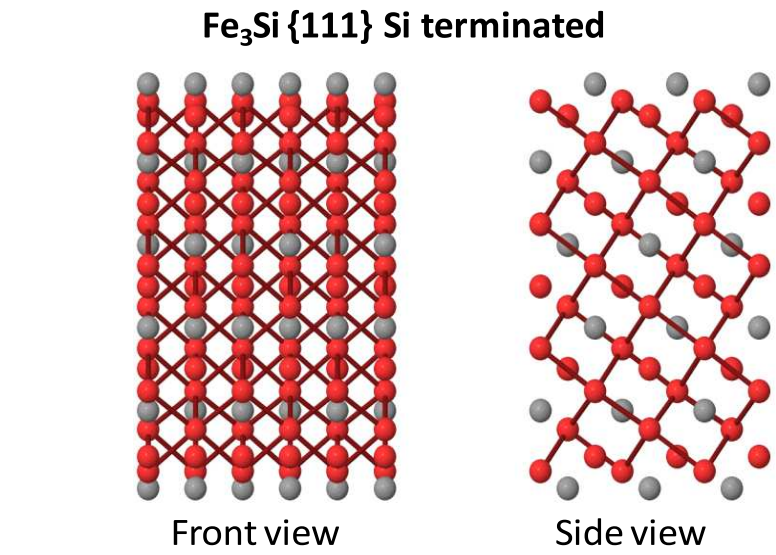
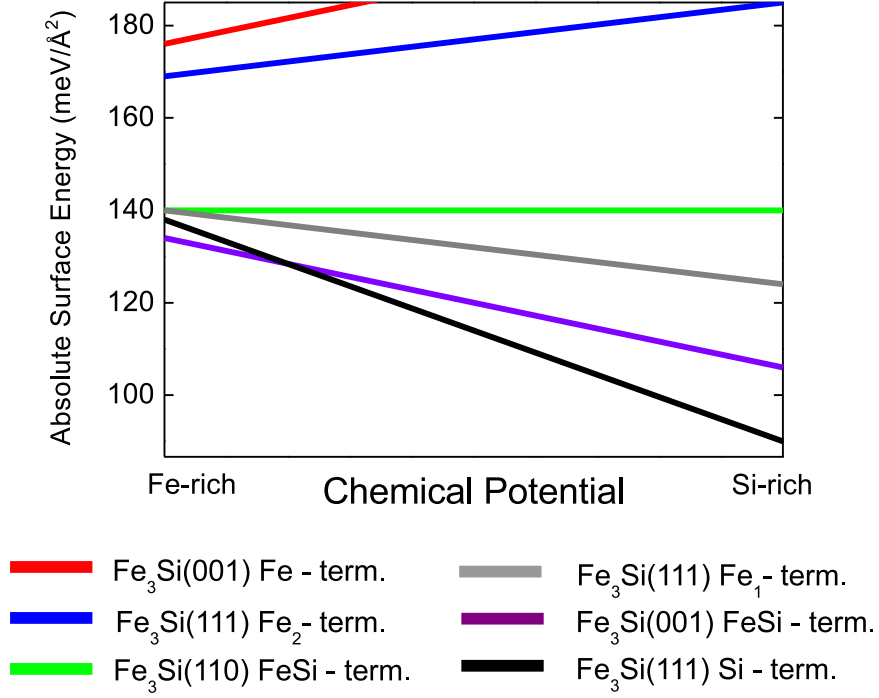


Figure 5. (color online) Surface energy of differently terminated (term.) surfaces calculated by DFT in generalized gradient approximation. The structure of the Si-terminated Fe<sub>3</sub>Si{111} surface is illustrated below, Fe atoms are symbolized as red balls whereas Si atoms as grey balls.